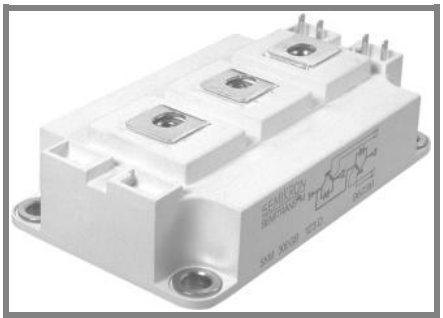
SKM 200GB126D ...



SEMITRANS® 3

Trench IGBT Modules

SKM 200GB126D

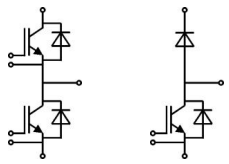
SKM 200GAL126D

Features

- Trench = Trenchgate technology
- $V_{CE(sat)}$ with positive temperature coefficient
- High short circuit capability, self limiting to 6 x I_C

Typical Applications*

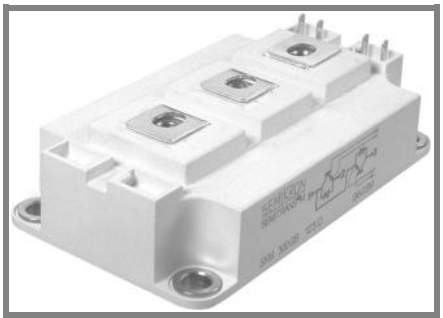
- Electronic welders
- AC inverter drives
- UPS



GB **GAL**

Absolute Maximum Ratings	T_{case} = 25°C, unless otherwise specified			
Symbol	**Conditions**		**Values**	**Units**
IGBT				
V_{CES}	T_j = 25 °C		1200	V
I_C	T_j = 150 °C	T_c = 25 °C	260	A
		T_c = 80 °C	190	A
I_{CRM}	I_{CRM}=2xI_{Cnom}		300	A
V_{GES}			± 20	V
t_{psc}	V_{CC} = 600 V; $V_{GE} \leq$ 20 V; V_{CES} < 1200 V	T_j = 125 °C	10	µs
Inverse Diode				
I_F	T_j = 150 °C	T_c = 25 °C	200	A
		T_c = 80 °C	140	A
I_{FRM}	I_{FRM}=2xI_{Fnom}		300	A
I_{FSM}	t_p = 10 ms; sin.	T_j = 150 °C	1100	A
Freewheeling Diode				
I_F	T_j = 150 °C	T_c = 25 °C	200	A
		T_c = 80 °C	140	A
I_{FRM}	I_{FRM}=2xI_{Fnom}		300	A
I_{FSM}	t_p = 10 ms; sin.	T_j = 150 °C	1100	A
Module				
$I_{t(RMS)}$			500	A
T_{vj}			- 40 ... + 150	°C
T_{stg}			- 40 ... + 125	°C
V_{isol}	AC, 1 min.		4000	V

Characteristics	T_{case} = 25°C, unless otherwise specified					
Symbol	**Conditions**		**min.**	**typ.**	**max.**	**Units**
IGBT						
$V_{GE(th)}$	V_{GE} = V_{CE}, I_C = 6 mA		5	5,8	6,5	V
I_{CES}	V_{GE} = 0 V, V_{CE} = V_{CES}	T_j = 25 °C		0,1	0,3	mA
		T_j = 125 °C				mA
V_{CE0}		T_j = 25 °C		1	1,2	V
		T_j = 125 °C		0,9	1,1	V
r_{CE}	V_{GE} = 15 V	T_j = 25°C		4,7	6,3	mΩ
		T_j = 125°C		7,3	9	mΩ
$V_{CE(sat)}$	I_{Cnom} = 150 A, V_{GE} = 15 V	T_j = 25°C$_{chiplev.}$		1,7	2,15	V
		T_j = 125°C$_{chiplev.}$		2	2,45	V
C_{ies}	V_{CE} = 25, V_{GE} = 0 V	f = 1 MHz		10,8		nF
C_{oes}				0,9		nF
C_{res}				0,9		nF
Q_G	V_{GE} = -8V - +20V			1530		nC
R_{Gint}	T_j = 25 °C			5		Ω
$t_{d(on)}$	R_{Gon} = 1,5 Ω	V_{CC} = 600V		260		ns
t_r		I_C= 150A		40		ns
E_{on}		T_j = 125 °C		18		mJ
$t_{d(off)}$	R_{Goff} = 1,5 Ω	V_{GE} = ±15V		540		ns
t_f				110		ns
E_{off}						mJ
$R_{th(j-c)}$	per IGBT				0,13	K/W



SEMITRANS® 3

Trench IGBT Modules

SKM 200GB126D

SKM 200GAL126D

Features

- Trench = Trenchgate technology
- $V_{CE(sat)}$ with positive temperature coefficient
- High short circuit capability, self limiting to 6 x I_C

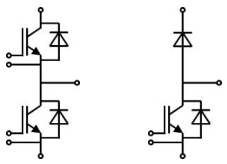
Typical Applications*

- Electronic welders
- AC inverter drives
- UPS

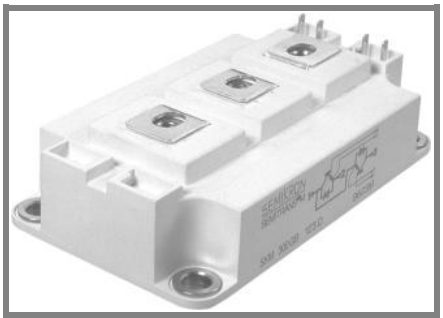
Characteristics						
Symbol	**Conditions**		**min.**	**typ.**	**max.**	**Units**
Inverse diode						
$V_F = V_{EC}$	I_{Fnom} = 150 A; V_{GE} = 0 V	T_j = 25 °C$_{chiplev.}$		1,6	1,8	V
		T_j = 125 °C$_{chiplev.}$		1,6	1,8	V
V_{F0}		T_j = 25 °C		1	1,1	V
		T_j = 125 °C		0,8	0,9	V
r_F		T_j = 25 °C		4	4,7	mΩ
		T_j = 125 °C		5,3	6	mΩ
I_{RRM}	I_F = 150 A	T_j = 125 °C		240		A
Q_{rr}	di/dt = 5000 A/µs			42		µC
E_{rr}	V_{GE} = -15 V; V_{CC} = 600 V					mJ
$R_{th(j-c)D}$	per diode				0,3	K/W
FWD						
$V_F = V_{EC}$	I_{Fnom} = 150 A; V_{GE} = 0 V	T_j = 25 °C$_{chiplev.}$		1,6	1,8	V
		T_j = 125 °C$_{chiplev.}$		1,6	1,8	V
V_{F0}		T_j = 25 °C		1	1,1	V
		T_j = 125 °C		0,8	0,9	V
r_F		T_j = 25 °C		4	4,7	V
		T_j = 125 °C		5,3	6	V
I_{RRM}	I_F = 150 A	T_j = 125 °C		240		A
Q_{rr}	di/dt = 5000 A/µs			42		µC
E_{rr}	V_{GE} = -15 V; V_{CC} = 600 V					mJ
$R_{th(j-c)FD}$	per diode				0,3	K/W
Module						
L_{CE}				15	20	nH
$R_{CC'+EE'}$	res., terminal-chip	T_{case}= 25 °C		0,35		mΩ
		T_{case}= 125 °C		0,5		mΩ
$R_{th(c-s)}$	per module				0,038	K/W
M_s	to heat sink M6		3		5	Nm
M_t	to terminals M5		2,5		5	Nm
w					325	g

This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our personal.



GB **GAL**



SEMITRANS® 3

Trench IGBT Modules

SKM 200GB126D

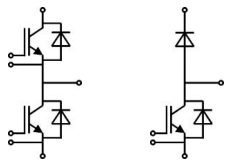
SKM 200GAL126D

Features

- Trench = Trenchgate technology
- $V_{CE(sat)}$ with positive temperature coefficient
- High short circuit capability, self limiting to 6 x I_C

Typical Applications*

- Electronic welders
- AC inverter drives
- UPS



GB **GAL**

Z_{th} Symbol	Conditions	Values	Units
$Z_{th(j-c)I}$			
R_i	i = 1	95	mk/W
R_i	i = 2	27	mk/W
R_i	i = 3	6,7	mk/W
R_i	i = 4	1,3	mk/W
tau_i	i = 1	0,0744	s
tau_i	i = 2	0,0087	s
tau_i	i = 3	0,002	s
tau_i	i = 4	0,0001	s
$Z_{th(j-c)D}$			
R_i	i = 1	200	mk/W
R_i	i = 2	80	mk/W
R_i	i = 3	17	mk/W
R_i	i = 4	3	mk/W
tau_i	i = 1	0,0536	s
tau_i	i = 2	0,0056	s
tau_i	i = 3	0,09	s
tau_i	i = 4	0,0002	s

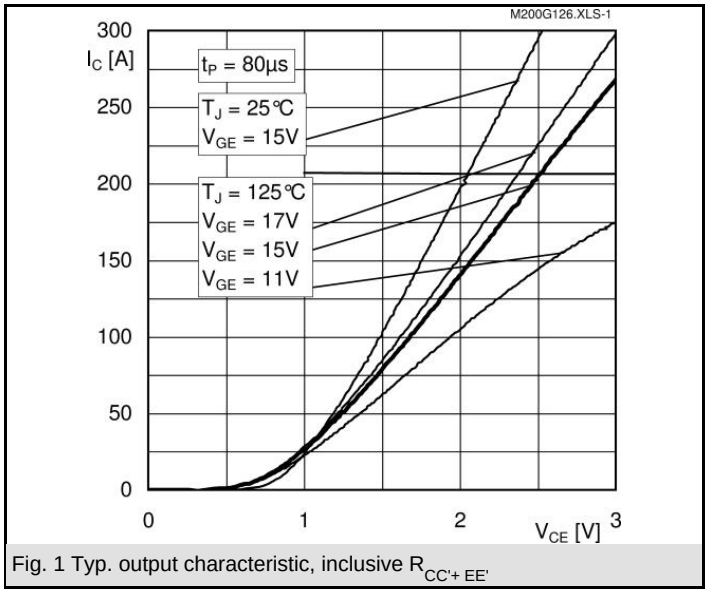


Fig. 1 Typ. output characteristic, inclusive $R_{CC'+EE'}$

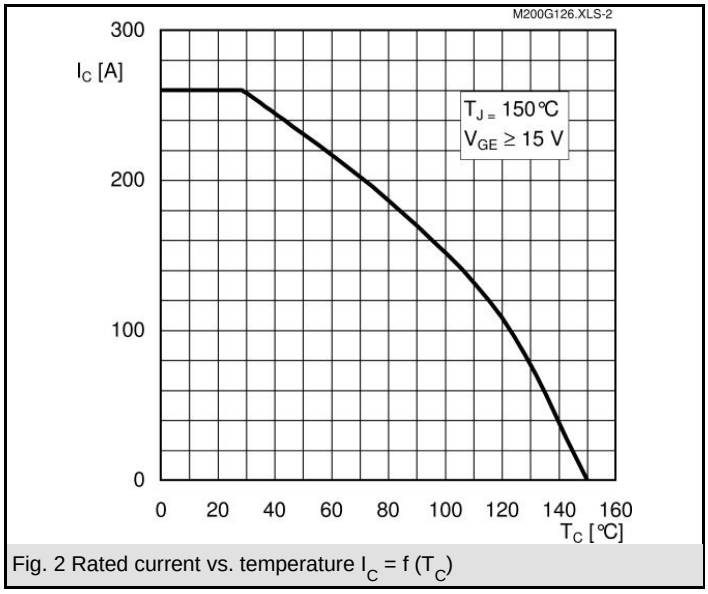


Fig. 2 Rated current vs. temperature $I_C = f(T_C)$

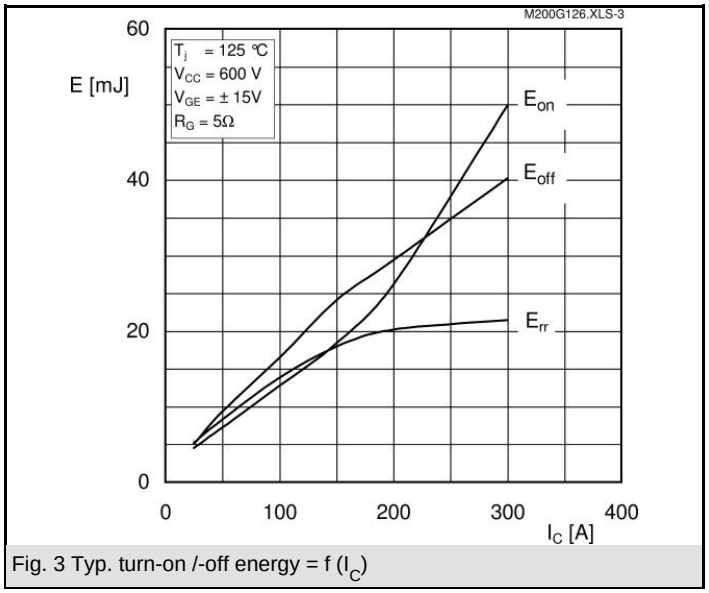


Fig. 3 Typ. turn-on /-off energy = f (I_C)

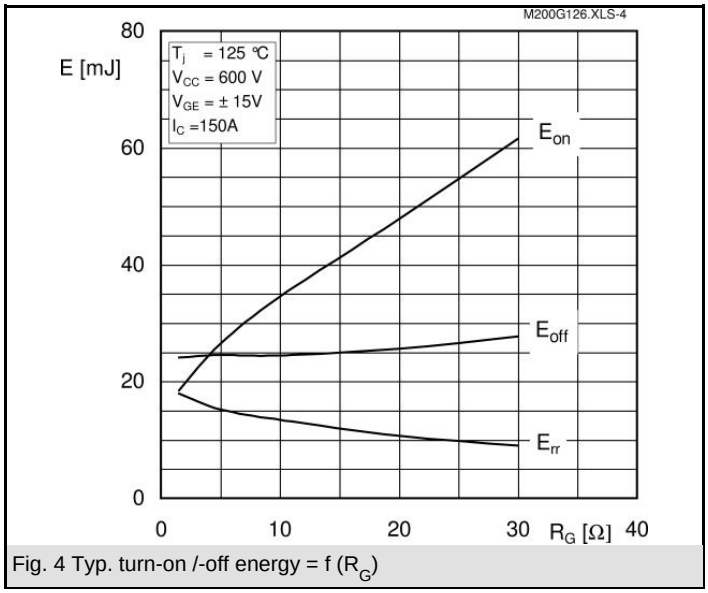


Fig. 4 Typ. turn-on /-off energy = f (R_G)

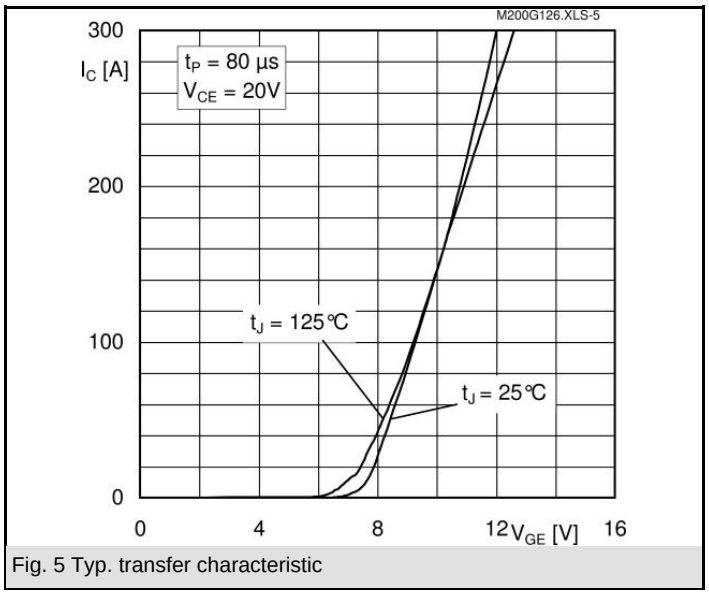


Fig. 5 Typ. transfer characteristic

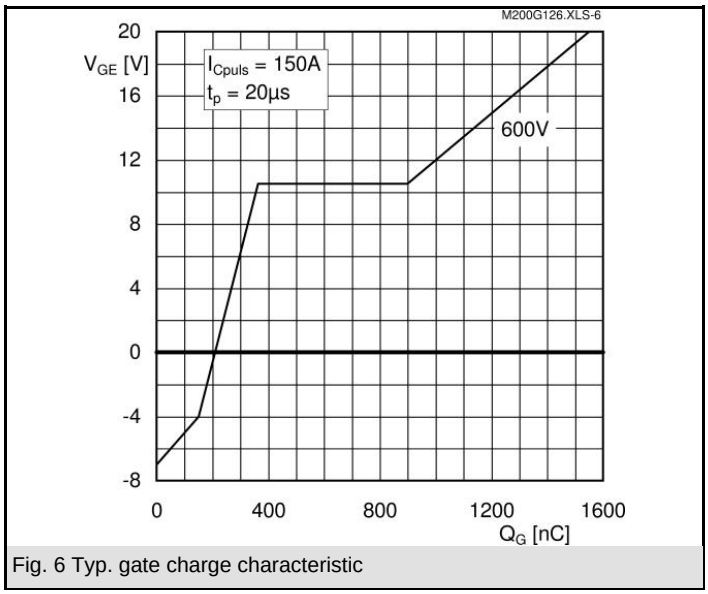


Fig. 6 Typ. gate charge characteristic

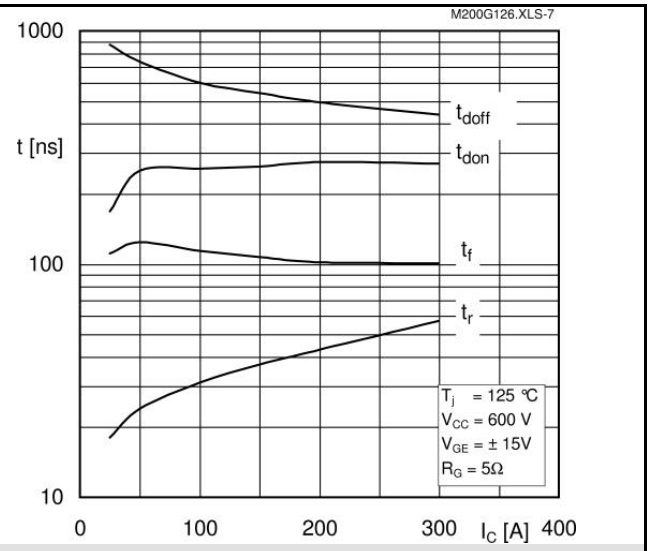


Fig. 7 Typ. switching times vs. I_C

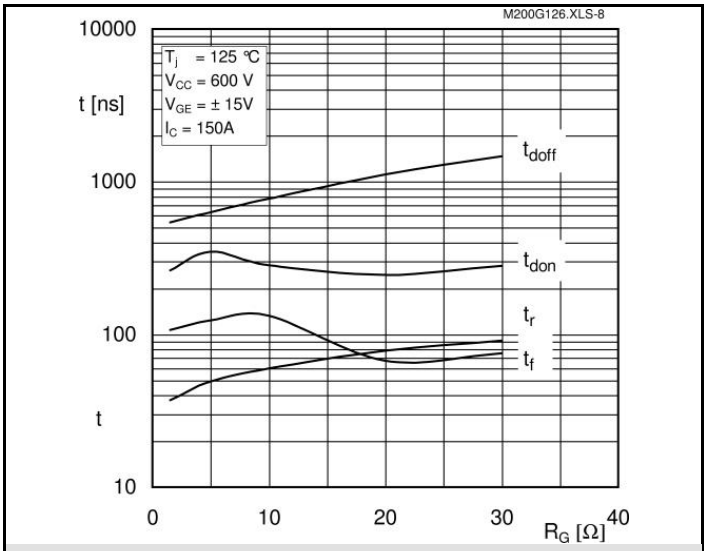


Fig. 8 Typ. switching times vs. gate resistor R_G

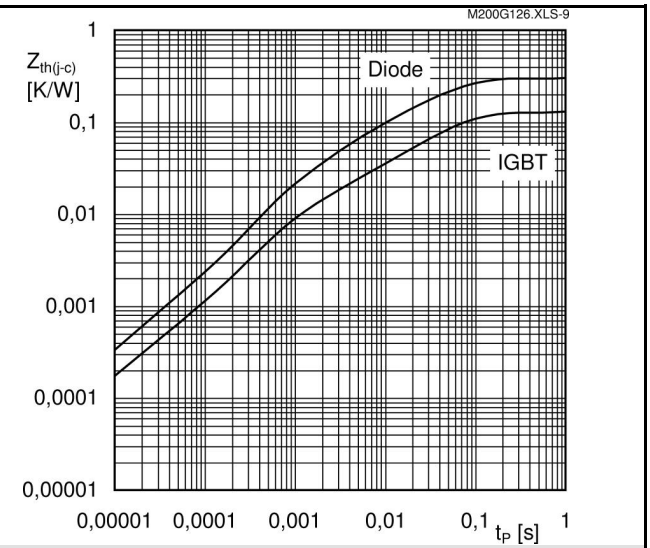


Fig. 9 Transient thermal impedance of IGBT

$Z_{thp(j-c)} = f(t_p)$; $D = t_p/t_c = t_p * f$

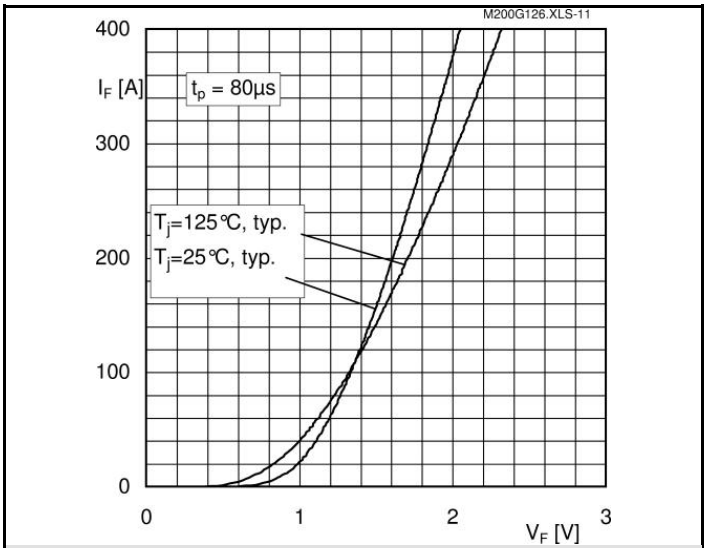


Fig. 10 Transient thermal impedance of FWD

$Z_{thp(j-c)} = f(t_p)$; $D = t_p/t_c = t_p * f$

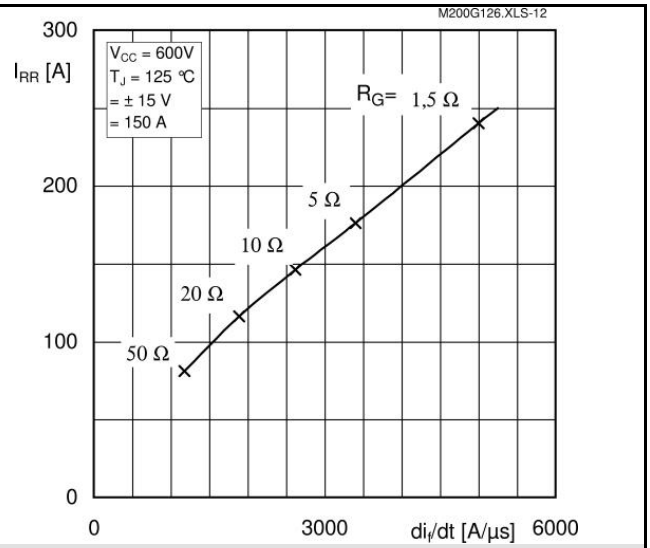


Fig. 11 CAL diode forward characteristic

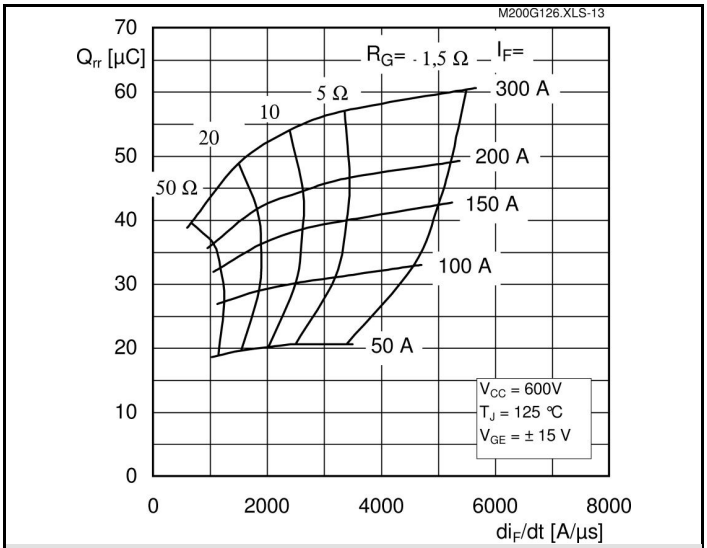
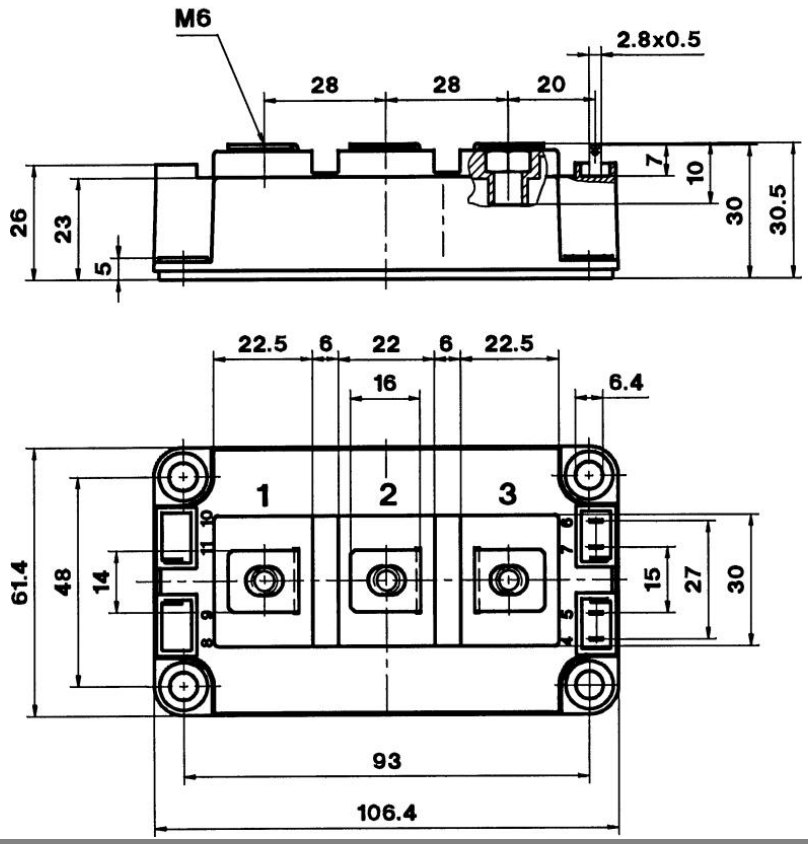


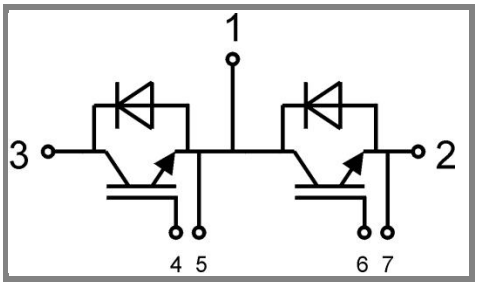
Fig. 12 Typ. CAL diode peak reverse recovery current

UL Recognized File 63 532

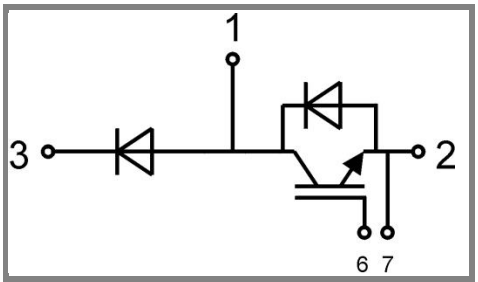
CASED56



Case D 56



Case D56 GB



Case D57 GAL

